

TOSHIBA Transistor Silicon PNP Epitaxial Type

2SA1837

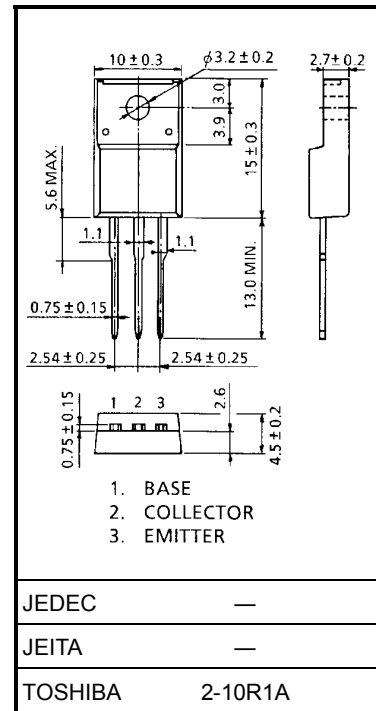
Power Amplifier Applications

Driver Stage Amplifier Applications

- High transition frequency: $f_T = 70$ MHz (typ.)
- Complementary to 2SC4793

Maximum Ratings (Tc = 25°C)

Characteristics		Symbol	Rating	Unit
Collector-base voltage		V_{CBO}	-230	V
Collector-emitter voltage		V_{CEO}	-230	V
Emitter-base voltage		V_{EBO}	-5	V
Collector current		I_C	-1	A
Base current		I_B	-0.1	A
Collector power dissipation	$T_a = 25^\circ\text{C}$	P_C	2.0	W
	$T_c = 25^\circ\text{C}$		20	
Junction temperature		T_j	150	$^\circ\text{C}$
Storage temperature range		T_{stg}	-55 to 150	$^\circ\text{C}$



Weight: 1.7 g (typ.)

Electrical Characteristics (Tc = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	$V_{CB} = -230\text{ V}, I_E = 0$	—	—	-1.0	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5\text{ V}, I_C = 0$	—	—	-1.0	μA
Collector-emitter breakdown voltage	$V_{(BR) CEO}$	$I_C = -10\text{ mA}, I_B = 0$	-230	—	—	V
DC current gain	h_{FE}	$V_{CE} = -5\text{ V}, I_C = -100\text{ mA}$	100	—	320	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500\text{ mA}, I_B = -50\text{ mA}$	—	—	-1.5	V
Base-emitter voltage	V_{BE}	$V_{CE} = -5\text{ V}, I_C = -500\text{ mA}$	—	—	-1.0	V
Transition frequency	f_T	$V_{CE} = -10\text{ V}, I_C = -100\text{ mA}$	—	70	—	MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10\text{ V}, I_C = 0, f = 1\text{ MHz}$	—	30	—	pF

Marking

